

ABSTRACT OF THE DISCLOSURE

A silicon single crystal wafer for a particle monitor is presented, which wafer has an extremely small amount in the surface density of light point defects and is capable of still maintaining a small surface density even after repeating the SC - 1. The wafer is prepared by slicing a silicon single crystal ingot including an area in which crystal originated particles are generated, and the surface density of particles having a size of not less than $0.12\text{ }\mu\text{m}$ is not more than 15 counts/cm^2 after repeating the SC - 1. More preferably, a silicon single crystal wafer having a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}\text{ atoms/cm}^3$ provides a surface density of not more than 1 counts/cm^2 for the particles having a diameter of not less than $0.12\text{ }\mu\text{m}$ even after repeating the SC - 1. Hence, a high quality wafer optimally used for a particle monitor can be obtained and a very small number of defects in the wafer make it possible to produce devices.